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International Bureau

INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification 6 :
C09K 3/14, C09G 1/02, H01L 21/321

A1

(11) International Publication Number: WO 00/00567

(43) International Publication Date: 6 January 2000 (06.01.00)

(21) International Application Number: PCT/US99/14557

(22) International Filing Date: 25 June 1999 (25.06.99)

(30) Priority Data:
09/105,555 26 June 1998 (26.06.98) US

(71) Applicant: CABOT CORPORATION [US/US]; 75 State Street, Boston, MA 02109–1806 (US).

(72) Inventors: KAUFMAN, Vlasta, Brusic; 721 Easton Avenue, Geneva, IL 60134 (US). KISTLER, Rodney, C.; 149 Forest Hill Drive, Los Jatos, CA 95032 (US). WANG, Shumin; 1006 Dakota Circle, Naperville, IL 60563 (US).

(74) Agent: LANDO, Michelle, B.; Cabot Corporation, 157 Concord Road, P.O. Box 7001, Billerica, MA 01821–7001 (US).

(81) Designated States: AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, CA, CH, CN, CZ, DE, DK, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MD, MG, MK, MN, MW, MX, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, UA, UG, UZ, VN, YU, ZA, ZW, ARIPO patent (GH, GM, KE, LS, MW, SD, SL, SZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).

Published
With international search report.

(54) Title: CHEMICAL MECHANICAL POLISHING SLURRY USEFUL FOR COPPER/TANTALUM SUBSTRATE

(57) Abstract

The present invention is a first CMP slurry including an abrasive, an oxidizing agent, a complexing agent, a film forming agent and an organic amino compound, a second polishing slurry including an abrasive, an oxidizing agent, and acetic acid wherein the weight ratio of the oxidizing agent to acetic acid is at least 10 and a method for using the first and second polishing slurries sequentially to polish a substrate containing copper and containing tantalum or tantalum nitride or both tantalum and tantalum nitride.